MC74AC20, MC74ACT20

Dual 4−Input NAND Gate

High−Performance Silicon−Gate CMOS

ON Semiconductor®

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Features

- Outputs Source/Sink 24 mA
- ′ACT20 Has TTL Compatible Inputs
- These are Pb−Free Devices

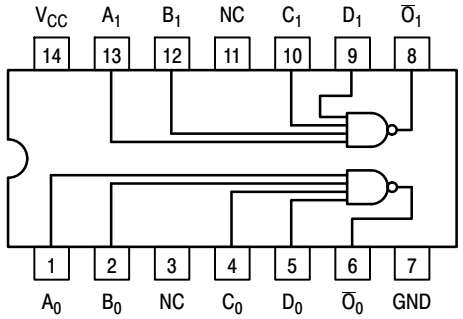
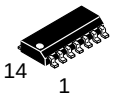


Figure 1. Pinout: 14-Lead Packages
(Top View)

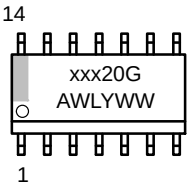
PIN ASSIGNMENT

PIN	FUNCTION
A_n, B_n, C_n, D_n	Inputs
$\overline{O}_n$	Outputs

MARKING DIAGRAM



SOIC−14
D SUFFIX
CASE 751A



xxx	= AC or ACT
A	= Assembly Location
WL	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	−0.5 to +7.0	V
V_I	DC Input Voltage	$-0.5 \le V_I \le V_{CC} + 0.5$	V
V_O	DC Output Voltage (Note 1)	$-0.5 \le V_O \le V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	±20	mA
I_{OK}	DC Output Diode Current	±50	mA
I_O	DC Output Sink/Source Current	±50	mA
I_{CC}	DC Supply Current per Output Pin	±50	mA
I_{GND}	DC Ground Current per Output Pin	±50	mA
T_{STG}	Storage Temperature Range	−65 to +150	°C
T_L	Lead temperature, 1 mm from Case for 10 Seconds	260	°C
T_J	Junction temperature under Bias	+150	°C
θ_{JA}	Thermal Resistance (Note 2)	125	°C/W
P_D	Power Dissipation in Still Air at 85°C	125	mW
MSL	Moisture Sensitivity	Level 1	
F_R	Flammability Rating Oxygen Index: 30% − 35%	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 2000 > 200 > 1000	V
$I_{Latch-Up}$	Latch−Up Performance Above V_{CC} and Below GND at 85°C (Note 6)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.
2. The package thermal impedance is calculated in accordance with JESD51−7.
3. Tested to EIA/JESD22−A114−A.
4. Tested to EIA/JESD22−A115−A.
5. Tested to JESD22−C101−A.
6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Typ	Min	Unit
V_{CC}	Supply Voltage	′AC	2.0	5.0	6.0	V
		′ACT	4.5	5.0	5.5	
VREG	DC Regulated Power Voltage (Ref. to GND)		0	−	V_{CC}	V
t_r, t_f	Input Rise and Fall Time (Note 1) ′AC Devices except Schmitt Inputs	V_{CC} @ 3.0 V	−	150	−	ns/V
		V_{CC} @ 4.5 V	−	40	−	
		V_{CC} @ 5.5 V	−	25	−	
t_r, t_f	Input Rise and Fall Time (Note 2) ′ACT Devices except Schmitt Inputs	V_{CC} @ 4.5 V	−	10	−	ns/V
		V_{CC} @ 5.5 V	−	8.0	−	
T_J	Junction Temperature (PDIP)		−	−	140	°C
T_A	Operating Ambient Temperature Range		−40	25	85	°C
I_{OH}	Output Current − HIGH		−	−	−24	mA
I_{OL}	Output Current − LOW		−	−	24	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. V_{in} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.
2. V_{in} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	74AC T_A = +25°C		74AC T_A = −40°C to +85°C	Unit	Conditions
			Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	V_{OUT} = 0.1 V or V_{CC} − 0.1 V
V_{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V_{OUT} = 0.1 V or V_{CC} − 0.1 V
V_{OH}	Minimum Low Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	I_{OUT} = − 50 μA
		3.0 4.5 5.5	− − −	2.56 3.86 4.86	2.46 3.76 4.76	V	*V_{IN} = V_{IL} or V_{IH} − 12 mA I_{OH} − 24 mA − 24 mA
V_{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	I_{OUT} = 50 μA
		3.0 4.5 5.5	− − −	0.36 0.36 0.36	0.44 0.44 0.44	V	*V_{IN} = V_{IL} or V_{IH} 12 mA I_{OL} 24 mA 24 mA
I_{IN}	Maximum Input Leakage Current	5.5	−	±0.1	±1.0	μA	V_I = V_{CC}, GND
I_{OLD}	†Minimum Dynamic Output Current	5.5	−	−	75	mA	V_{OLD} = 1.65 V Max
I_{OHD}		5.5	−	−	−75	mA	V_{OHD} = 3.85 V Min
I_{CC}	Maximum Quiescent Supply Current	5.5	−	4.0	40	μA	V_{IN} = V_{CC} or GND

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
*All outputs loaded; thresholds on input associated with output under test.
†Maximum test duration 2.0 ms, one output loaded at a time.

NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V.

AC CHARACTERISTICS

Symbol	Parameter	V_{CC}* (V)	74AC T_A = +25°C C_L = 50 pF			74AC T_A = −40°C to +85°C C_L = 50 pF		Unit
			Min	Typ	Max	Min	Max	
t_{PLH}	Propagation Delay	3.3 5.0	2.0 1.5	6.0 5.0	8.5 7.0	1.5 1.0	10.0 8.0	ns
t_{PHL}	Propagation Delay	3.3 5.0	1.5 1.5	5.0 4.0	7.0 6.0	1.0 1.0	9.0 7.0	ns

*Voltage Range 3.3 V is 3.3 V ±0.3 V.
Voltage Range 5.0 V is 5.0 V ±0.5 V.

DC CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	74ACT		74ACT	Unit	Conditions
			T_A = +25°C		T_A = −40°C to +85°C		
			Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V_{OUT} = 0.1 V or V_{CC} − 0.1 V
V_{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V_{OUT} = 0.1 V or V_{CC} − 0.1 V
V_{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I_{OUT} = − 50 μA
		4.5 5.5	− −	3.86 4.86	3.76 4.76	V	*V_{IN} = V_{IL} or V_{IH} I_{OH} − 24 mA I_{OH} − 24 mA
V_{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I_{OUT} = 50 μA
		4.5 5.5	− −	0.36 0.36	0.44 0.44	V	*V_{IN} = V_{IL} or V_{IH} I_{OH} 24 mA I_{OH} 24 mA
I_{IN}	Maximum Input Leakage Current	5.5	−	±0.1	±1.0	μA	V_I = V_{CC}, GND
ΔI_{CCT}	Additional Max. I_{CC}/Input	5.5	0.6	−	1.5	mA	V_I = V_{CC} − 2.1 V
I_{OLD}	†Minimum Dynamic Output Current	5.5	−	−	75	mA	V_{OLD} = 1.65 V Max
I_{OHD}		5.5	−	−	−75	mA	V_{OHD} = 3.85 V Min
I_{CC}	Maximum Quiescent Supply Current	5.5	−	4.0	40	μA	V_{IN} = V_{CC} or GND

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
*All outputs loaded; thresholds on input associated with output under test.
†Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS

Symbol	Parameter	V_{CC}* (V)	74ACT			74ACT		Unit
			T_A = +25°C C_L = 50 pF			T_A = −40°C to +85°C C_L = 50 pF		
			Min	Typ	Max	Min	Max	
t_{PLH}	Propagation Delay	5.0	2.0	6.5	9.0	1.5	10.5	ns
t_{PHL}	Propagation Delay	5.0	2.0	5.5	9.0	1.5	10.5	ns

*Voltage Range 5.0 V is 5.0 V ±0.5 V.

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C_{IN}	Input Capacitance	4.5	pF	V_{CC} = 5.0 V
C_{PD}	Power Dissipation Capacitance	40	pF	V_{CC} = 5.0 V

ORDERING INFORMATION

Device	Package	Shipping†
MC74AC20DG	SOIC−14 (Pb−Free)	55 Units/Rail
MC74AC20DR2G	SOIC−14 (Pb−Free)	2500/Tape & Reel
MC74ACT20DG	SOIC−14 (Pb−Free)	55 Units/Rail
MC74ACT20DR2G	SOIC−14 (Pb−Free)	2500/Tape & Reel

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

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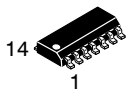
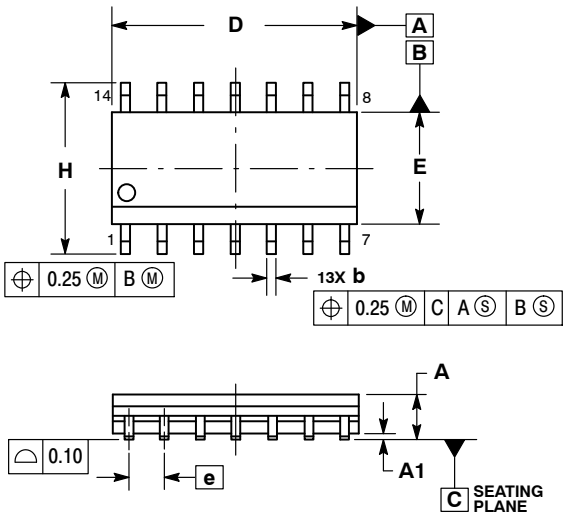
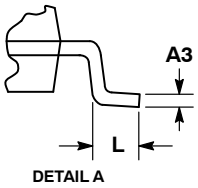


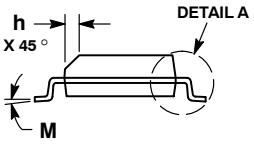
SCALE 1:1

SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016



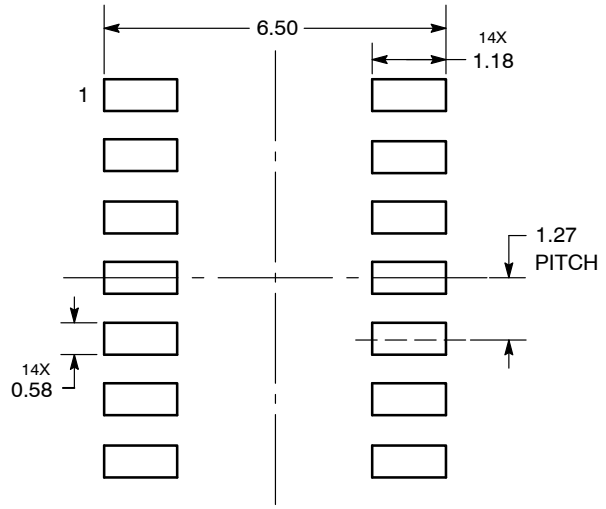




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

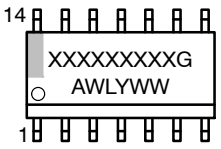
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC−14 NB		PAGE 1 OF 2

SOIC−14
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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